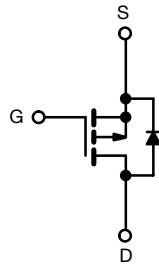


Power MOSFET



P-Channel MOSFET

FEATURES

- Advanced process technology
- Fully avalanche rated
- Surface-mount (IRFR9310, SiHFR9310)
- Straight lead (IRFU9310, SiHFU9310)
- P-channel
- Fast switching
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
Available

DESCRIPTION

Third generation power MOSFETs from Vishay utilize advanced processing techniques to achieve low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The DPAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU/SiHFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 W are possible in typical surface-mount applications.

PRODUCT SUMMARY

| | | |
|---------------------------|------------------|-----|
| V_{DS} (V) | -400 | |
| $R_{DS(on)}$ (Ω) | $V_{GS} = -10$ V | 7.0 |
| Q_g (Max.) (nC) | 13 | |
| Q_{gs} (nC) | 3.2 | |
| Q_{gd} (nC) | 5.0 | |
| Configuration | Single | |

ORDERING INFORMATION

| Package | DPAK (TO-252) | DPAK (TO-252) | DPAK (TO-252) | DPAK (TO-252) | IPAK (TO-251) |
|---------------------------------|---------------|-----------------------------|----------------------------|-----------------------------|---------------|
| Lead (Pb)-free and halogen-free | SiHFR9310-GE3 | SiHFR9310TRL-GE3 | SiHFR9310TR-GE3 | SiHFR9310TRR-GE3 | SiHFU9310-GE3 |
| Lead (Pb)-free | IRFR9310PbF | IRFR9310TRLPbF ^a | IRFR9310TRPbF ^a | IRFR9310TRRPbF ^a | IRFU9310PbF |

Note

- a. See device orientation

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

| PARAMETER | SYMBOL | LIMIT | UNIT | |
|---|----------------|-------------------|----------------|---|
| Drain-source voltage | V_{DS} | -400 | V | |
| Gate-source voltage | V_{GS} | ± 20 | | |
| Continuous drain current | I_D | V_{GS} at -10 V | $T_C = 25$ °C | A |
| | | | $T_C = 100$ °C | |
| Pulsed drain current ^a | I_{DM} | -7.2 | | |
| Linear derating factor | | 0.40 | W/°C | |
| Single pulse avalanche energy ^b | E_{AS} | 92 | mJ | |
| Repetitive avalanche current ^a | I_{AR} | -1.8 | A | |
| Repetitive avalanche energy ^a | E_{AR} | 5.0 | mJ | |
| Maximum power dissipation | P_D | 50 | W | |
| Peak diode recovery dV/dt ^c | dV/dt | -24 | V/ns | |
| Operating junction and storage temperature range | T_J, T_{stg} | -55 to +150 | °C | |
| Soldering recommendations (peak temperature) ^d | For 10 s | 300 | | |

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
 b. Starting $T_J = 25$ °C, $L = 57$ mH, $R_g = 25$ Ω , $I_{AS} = -1.8$ A (see fig. 12)
 c. $I_{SD} \leq -1.1$ A, $dI/dt \leq 450$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C
 d. 1.6 mm from case



| THERMAL RESISTANCE RATINGS | | | | | |
|--|------------|------|------|------|------|
| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Maximum junction-to-ambient | R_{thJA} | - | - | 110 | °C/W |
| Maximum junction-to-ambient (PCB mount) ^a | R_{thJA} | - | - | 50 | |
| Maximum junction-to-case (drain) | R_{thJC} | - | - | 2.5 | |

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material)

| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | |
|---|---------------------|---|--|------|-------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | | |
| Drain-source breakdown voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$ | | -400 | - | - | V |
| V_{DS} temperature coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}, I_D = -1\text{ mA}$ | | - | -0.41 | - | V/°C |
| Gate-source threshold voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$ | | -2.0 | - | -4.0 | V |
| Gate-source leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | | - | - | ± 100 | nA |
| Zero gate voltage drain current | I_{DSS} | $V_{DS} = -400\text{ V}, V_{GS} = 0\text{ V}$ | | - | - | -100 | μA |
| | | $V_{DS} = -320\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | | - | - | -500 | |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS} = -10\text{ V}$ | $I_D = -1.1\text{ A}^b$ | - | - | 7.0 | Ω |
| Forward transconductance | g_{fs} | $V_{DS} = -50\text{ V}, I_D = -1.1\text{ A}$ | | 0.91 | - | - | S |
| Dynamic | | | | | | | |
| Input capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1.0\text{ MHz}, \text{ see fig. 5}$ | | - | 270 | - | pF |
| Output capacitance | C_{oss} | | | - | 50 | - | |
| Reverse transfer capacitance | C_{rss} | | | - | 8.0 | - | |
| Total gate charge | Q_g | $V_{GS} = -10\text{ V}$ | $I_D = -1.1\text{ A}, V_{DS} = -320\text{ V}, \text{ see fig. 6 and 13}^b$ | - | - | 13 | nC |
| Gate-source charge | Q_{gs} | | | - | - | 3.2 | |
| Gate-drain charge | Q_{gd} | | | - | - | 5.0 | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = -200\text{ V}, I_D = -1.1\text{ A}, R_g = 21\text{ }\Omega, R_D = 180\text{ }\Omega, \text{ see fig. 10}^b$ | | - | 11 | - | ns |
| Rise time | t_r | | | - | 10 | - | |
| Turn-off delay time | $t_{d(off)}$ | | | - | 25 | - | |
| Fall time | t_f | | | - | 24 | - | |
| Internal drain inductance | L_D | Between lead, 6 mm (0.25") from package and center of die contact ^c | | - | 4.5 | - | nH |
| Internal source inductance | L_S | | | - | 7.5 | - | |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous source-drain diode current | I_S | MOSFET symbol showing the integral reverse p-n junction diode | | - | - | -1.9 | A |
| Pulsed diode forward current ^a | I_{SM} | | | - | - | -7.6 | |
| Body diode voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}, I_S = -1.1\text{ A}, V_{GS} = 0\text{ V}^b$ | | - | - | -4.0 | V |
| Body diode reverse recovery time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}, I_F = -1.1\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$ | | - | 170 | 260 | ns |
| Body diode reverse recovery charge | Q_{rr} | | | - | 640 | 960 | nC |
| Forward turn-on time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D) | | | | | |

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$
- c. This is applied for IPAK, L_S of DPAK is measured between lead and center of die contact



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

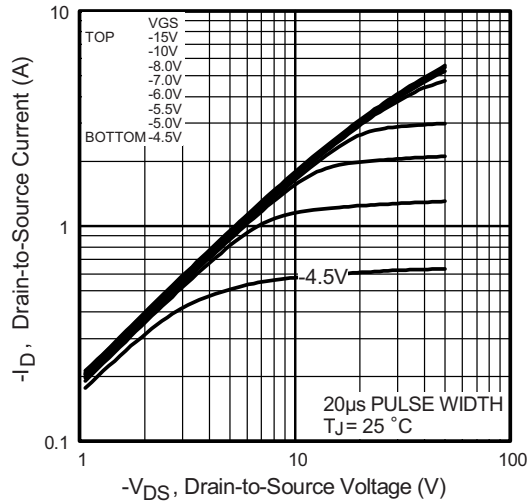


Fig. 1 - Typical Output Characteristics

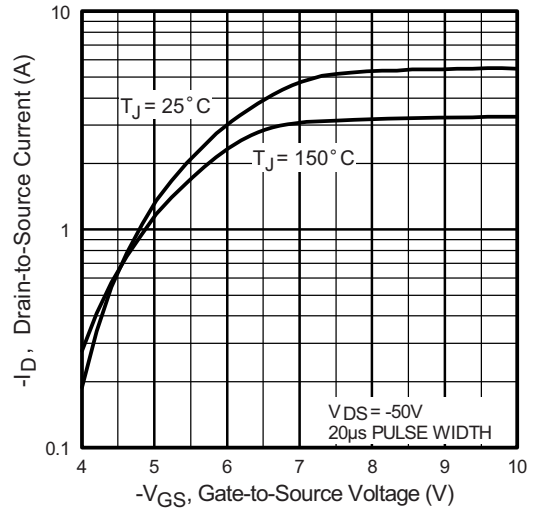


Fig. 2 - Typical Transfer Characteristics

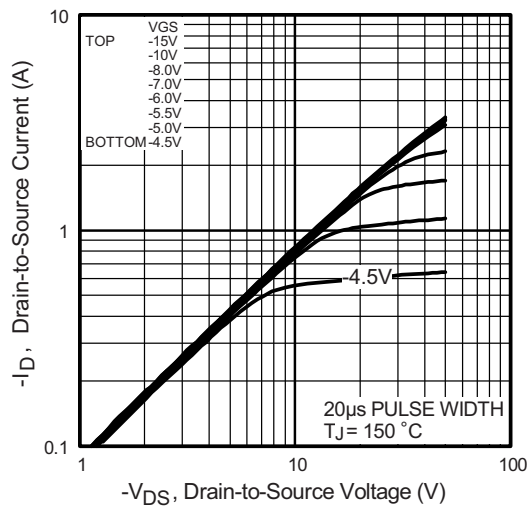


Fig. 1 - Typical Output Characteristics

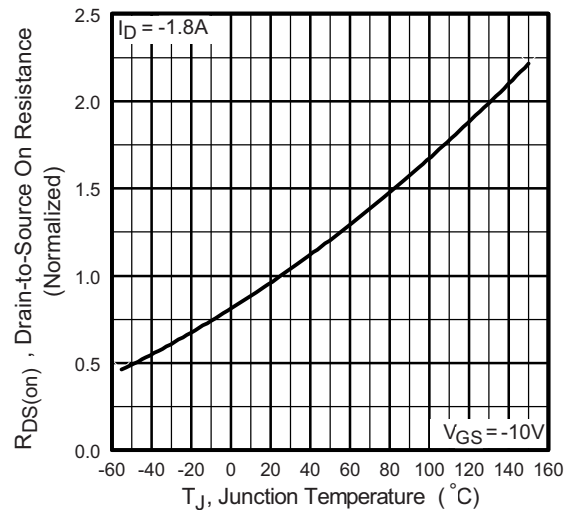


Fig. 3 - Normalized On-Resistance vs. Temperature

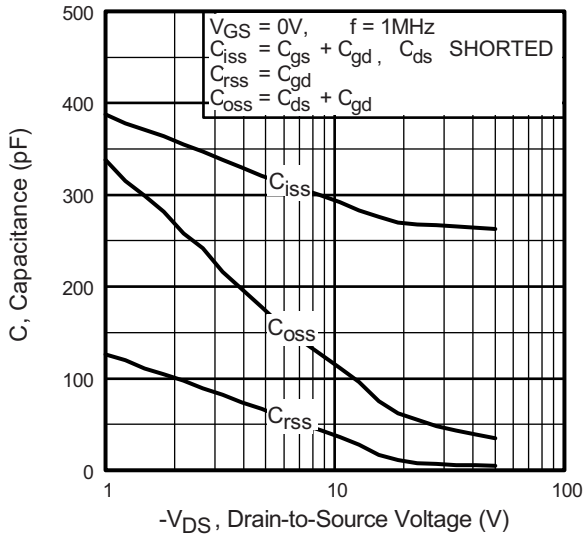


Fig. 4 - Typical Capacitance vs. Drain-to-Source Voltage

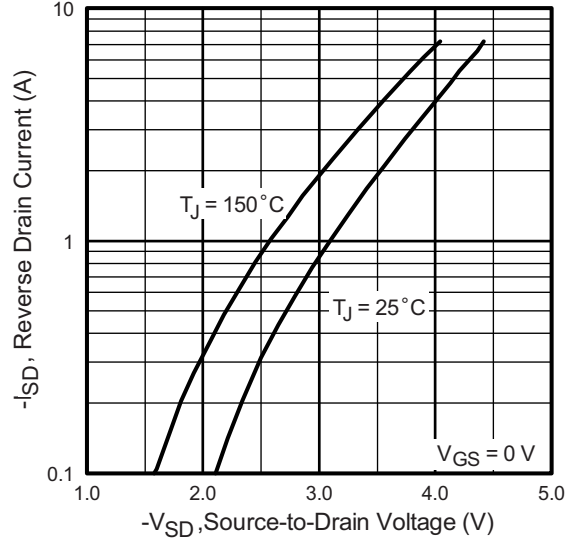


Fig. 6 - Typical Source-Drain Diode Forward Voltage

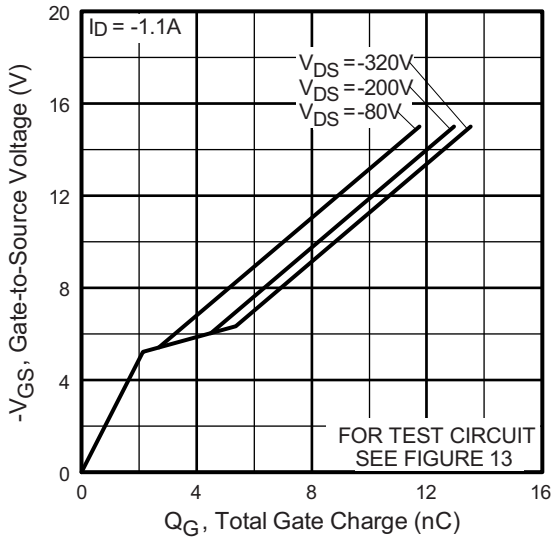


Fig. 5 - Typical Gate Charge vs. Gate-to-Source Voltage

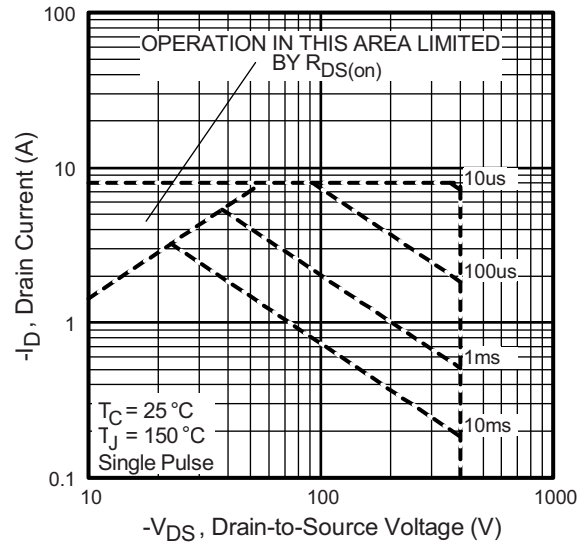


Fig. 7 - Maximum Safe Operating Area

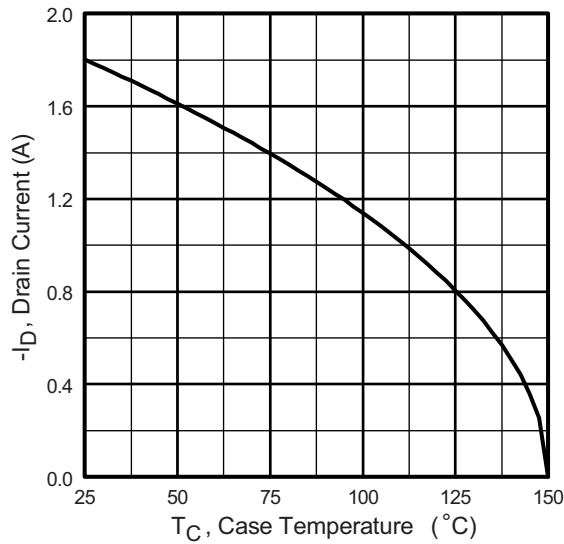


Fig. 8 - Maximum Drain Current vs. Case Temperature

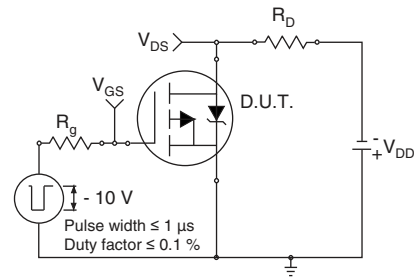


Fig. 10a - Switching Time Test Circuit

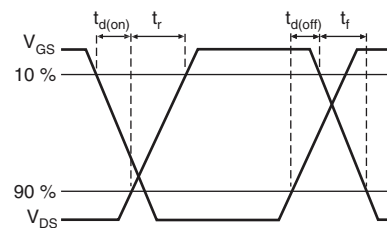


Fig. 10b - Switching Time Waveforms

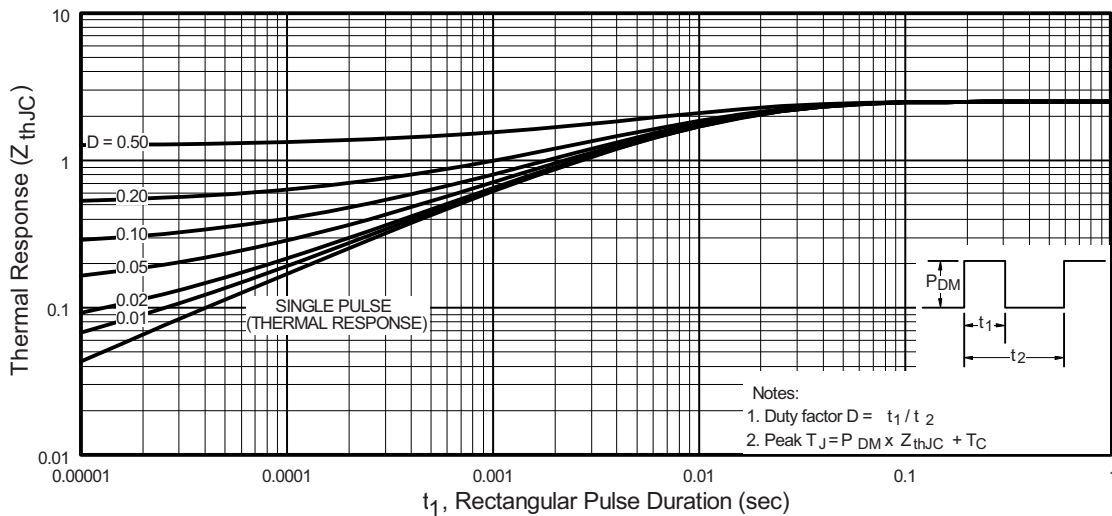
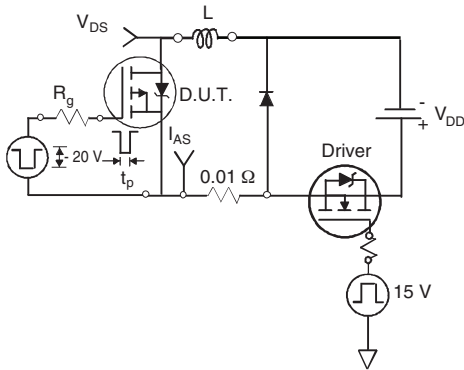
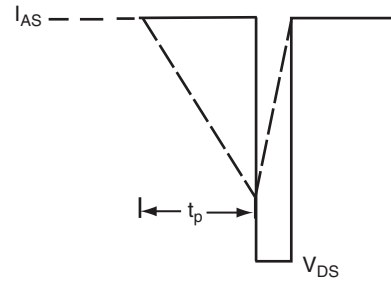
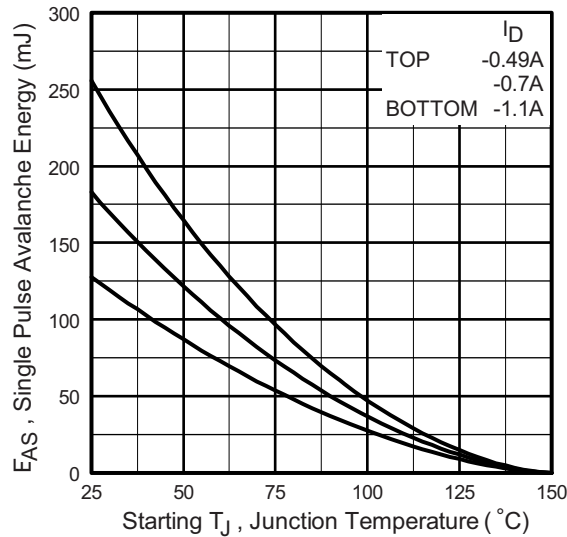
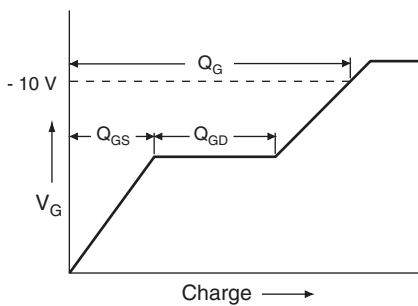
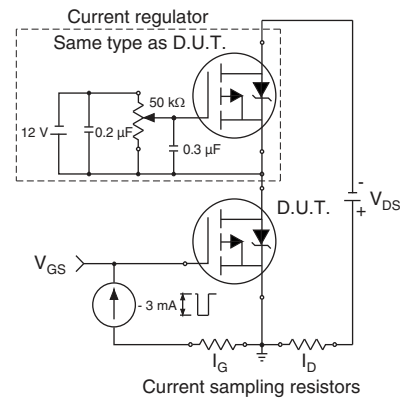
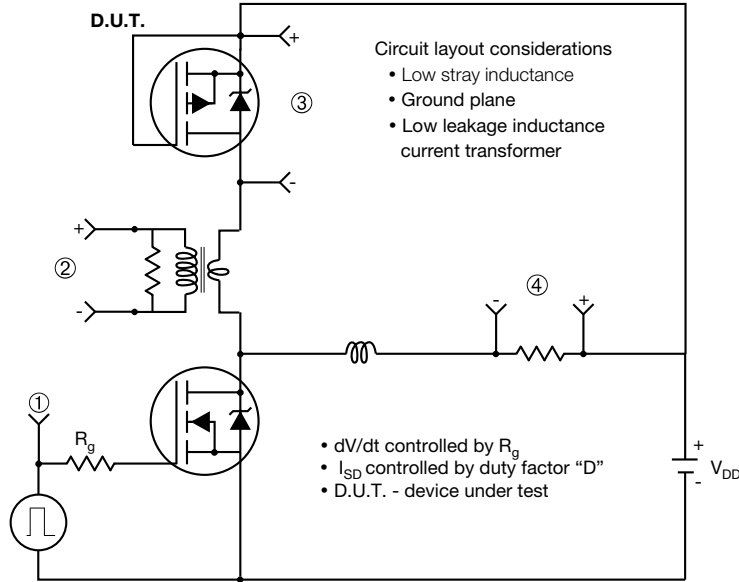


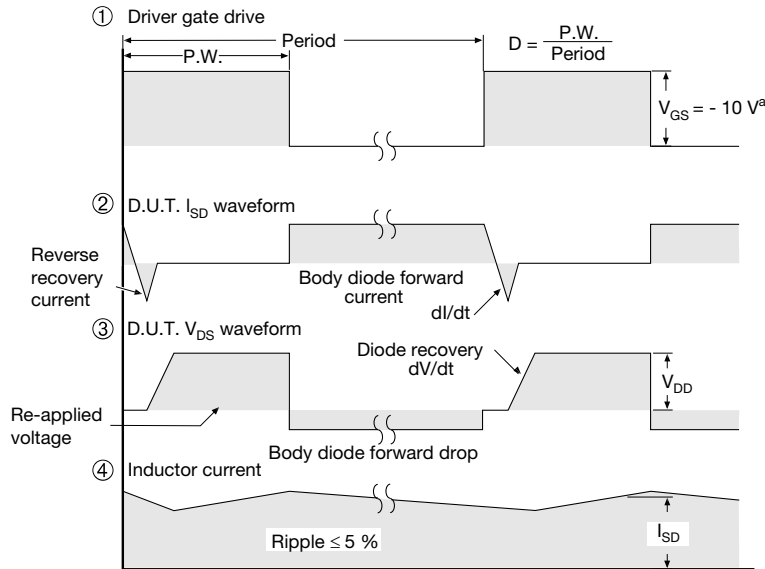
Fig. 9 - Maximum Effective Transient Thermal Impedance, Junction-to-Case


Fig. 12a - Unclamped Inductive Test Circuit

Fig. 12b - Unclamped Inductive Waveforms

Fig. 12c - Maximum Avalanche Energy vs. Drain Current

Fig. 13a - Basic Gate Charge Waveform

Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note
• Compliment N-Channel of D.U.T. for driver



Note
a. $V_{GS} = -5\text{ V}$ for logic level and -3 V drive devices

Fig. 10 - For P-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91284.



TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y



| MILLIMETERS | | |
|-------------|----------|-------|
| DIM. | MIN. | MAX. |
| A | 2.18 | 2.38 |
| A1 | - | 0.127 |
| b | 0.64 | 0.88 |
| b2 | 0.76 | 1.14 |
| b3 | 4.95 | 5.46 |
| C | 0.46 | 0.61 |
| C2 | 0.46 | 0.89 |
| D | 5.97 | 6.22 |
| D1 | 4.10 | - |
| E | 6.35 | 6.73 |
| E1 | 4.32 | - |
| H | 9.40 | 10.41 |
| e | 2.28 BSC | |
| e1 | 4.56 BSC | |
| L | 1.40 | 1.78 |
| L3 | 0.89 | 1.27 |
| L4 | - | 1.02 |
| L5 | 1.01 | 1.52 |

Note

- Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



| MILLIMETERS | | |
|-------------|----------|-------|
| DIM. | MIN. | MAX. |
| A | 2.18 | 2.39 |
| A1 | - | 0.13 |
| b | 0.65 | 0.89 |
| b1 | 0.64 | 0.79 |
| b2 | 0.76 | 1.13 |
| b3 | 4.95 | 5.46 |
| c | 0.46 | 0.61 |
| c1 | 0.41 | 0.56 |
| c2 | 0.46 | 0.60 |
| D | 5.97 | 6.22 |
| D1 | 5.21 | - |
| E | 6.35 | 6.73 |
| E1 | 4.32 | - |
| e | 2.29 BSC | |
| H | 9.94 | 10.34 |

| MILLIMETERS | | |
|-------------|-----------|------|
| DIM. | MIN. | MAX. |
| L | 1.50 | 1.78 |
| L1 | 2.74 ref. | |
| L2 | 0.51 BSC | |
| L3 | 0.89 | 1.27 |
| L4 | - | 1.02 |
| L5 | 1.14 | 1.49 |
| L6 | 0.65 | 0.85 |
| θ | 0° | 10° |
| θ1 | 0° | 15° |
| θ2 | 25° | 35° |

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022
 DWG: 5347

Case Outline for TO-251AA (High Voltage)

OPTION 1:



| DIM. | MILLIMETERS | | INCHES | |
|------|-------------|------|--------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 2.18 | 2.39 | 0.086 | 0.094 |
| A1 | 0.89 | 1.14 | 0.035 | 0.045 |
| b | 0.64 | 0.89 | 0.025 | 0.035 |
| b1 | 0.65 | 0.79 | 0.026 | 0.031 |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 |
| b3 | 0.76 | 1.04 | 0.030 | 0.041 |
| b4 | 4.95 | 5.46 | 0.195 | 0.215 |
| c | 0.46 | 0.61 | 0.018 | 0.024 |
| c1 | 0.41 | 0.56 | 0.016 | 0.022 |
| c2 | 0.46 | 0.86 | 0.018 | 0.034 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |

| DIM. | MILLIMETERS | | INCHES | |
|------|-------------|------|----------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| D1 | 5.21 | - | 0.205 | - |
| E | 6.35 | 6.73 | 0.250 | 0.265 |
| E1 | 4.32 | - | 0.170 | - |
| e | 2.29 BSC | | 2.29 BSC | |
| L | 8.89 | 9.65 | 0.350 | 0.380 |
| L1 | 1.91 | 2.29 | 0.075 | 0.090 |
| L2 | 0.89 | 1.27 | 0.035 | 0.050 |
| L3 | 1.14 | 1.52 | 0.045 | 0.060 |
| θ1 | 0° | 15° | 0° | 15° |
| θ2 | 25° | 35° | 25° | 35° |

ECN: E21-0682-Rev. C, 27-Dec-2021
DWG: 5968

Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Dimension are shown in inches and millimeters
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.13 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Thermal pad contour optional with dimensions b4, L2, E1 and D1
- Lead dimension uncontrolled in L3
- Dimension b1, b3 and c1 apply to base metal only
- Outline conforms to JEDEC® outline TO-251AA



OPTION 2: FACILITY CODE = N



| DIM. | MIN. | NOM. | MAX. |
|------|-------|-------|-------|
| A | 2.180 | 2.285 | 2.390 |
| A1 | 0.890 | 1.015 | 1.140 |
| b | 0.640 | 0.765 | 0.890 |
| b1 | 0.640 | 0.715 | 0.790 |
| b2 | 0.760 | 0.950 | 1.140 |
| b3 | 0.760 | 0.900 | 1.040 |
| b4 | 4.950 | 5.205 | 5.460 |
| c | 0.460 | - | 0.610 |
| c1 | 0.410 | - | 0.560 |
| c2 | 0.460 | - | 0.610 |
| D | 5.970 | 6.095 | 6.220 |
| D1 | 4.300 | - | - |

| DIM. | MIN. | NOM. | MAX. |
|------------|----------|-------|-------|
| D2 | 5.380 | - | - |
| E | 6.350 | 6.540 | 6.730 |
| E1 | 4.32 | - | - |
| e | 2.29 BSC | | |
| L | 8.890 | 9.270 | 9.650 |
| L1 | 1.910 | 2.100 | 2.290 |
| L2 | 0.890 | 1.080 | 1.270 |
| L3 | 1.140 | 1.330 | 1.520 |
| L4 | 1.300 | 1.400 | 1.500 |
| θ_1 | 0° | 7.5° | 15° |
| θ_2 | 4° | - | - |

ECN: E21-0682-Rev. C, 27-Dec-2021
DWG: 5968

Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- All dimension are in millimeters, angles are in degrees
- Heat sink side flash is max. 0.8 mm

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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